**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a 6 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Ultra small package: 0.98 × 1.48 × 0.35 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- · Battery switch
- · High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-12	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-8.2	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -3.0 A; $T_j$ = 25 °C		-	19	25	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
A1	G	gate	1 2	D I
A2	S	source	A \ \ \ \ \ \	
B1	S	source	В	$G \left( \begin{array}{c} \Psi \\ \overline{\Psi} \end{array} \right)$
B2	S	source	c	\ <del>\\</del>
C1	D	drain		
C2	D	drain	Transparent top view WLCSP6 (OL- PMCM6501VPE)	S 017aaa259

## 6. Ordering information

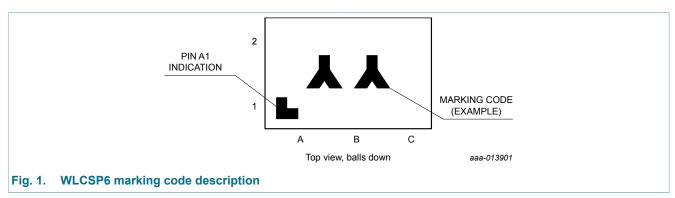
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMCM6501VPE	WLCSP6	WLCSP6: wafer level chip-size package; 6 bumps (3 x 2)	OL-PMCM6501VPE		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMCM6501VPE	AD



## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	-12	V
gate-source voltage			-8	8	V
drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-8.2	Α
	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-6.2	Α
	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-4	Α
peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	-25	Α
total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	556	mW
		[1]	-	1300	mW
	T <sub>sp</sub> = 25 °C		-	12500	mW
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode	1	1			1
source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.2	Α
	drain-source voltage gate-source voltage drain current  peak drain current total power dissipation  junction temperature ambient temperature storage temperature	$ \begin{array}{ll} \text{drain-source voltage} & T_j = 25  ^{\circ}\text{C} \\ \\ \text{gate-source voltage} \\ \\ \text{drain current} & V_{GS} = -4.5  \text{V};  T_{amb} = 25  ^{\circ}\text{C};  \text{t} \leq 5  \text{s} \\ \\ \hline V_{GS} = -4.5  \text{V};  T_{amb} = 25  ^{\circ}\text{C} \\ \\ \hline V_{GS} = -4.5  \text{V};  T_{amb} = 100  ^{\circ}\text{C} \\ \\ \hline V_{GS} = -4.5  \text{V};  T_{amb} = 100  ^{\circ}\text{C} \\ \\ \hline peak  \text{drain current} & T_{amb} = 25  ^{\circ}\text{C};  \text{single pulse};  t_p \leq 10  \mu\text{s} \\ \\ \hline total  \text{power dissipation} & T_{amb} = 25  ^{\circ}\text{C} \\ \\ \hline T_{sp} = 25  ^{\circ}\text{C} \\ \\ \hline \text{junction temperature} \\ \\ \hline \text{ambient temperature} \\ \\ \hline \text{storage temperature} \\ \\ \hline \\ \textbf{Sliode} \\ \\ \end{array} $	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \\ \text{drain current} \\ \\ \hline \\ V_{GS} = -4.5 \text{ V}; \ T_{amb} = 25  ^{\circ}\text{C}; \ t \leq 5 \text{ s} \\ \hline \\ V_{GS} = -4.5 \text{ V}; \ T_{amb} = 25  ^{\circ}\text{C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; \ T_{amb} = 25  ^{\circ}\text{C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; \ T_{amb} = 100  ^{\circ}\text{C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; \ T_{amb} = 100  ^{\circ}\text{C} \\ \hline \\ \text{peak drain current} \\ \hline \\ \text{total power dissipation} \\ \hline \\ T_{amb} = 25  ^{\circ}\text{C}; \ \text{single pulse}; \ t_p \leq 10  \mu\text{s} \\ \hline \\ T_{amb} = 25  ^{\circ}\text{C} \\ \hline \\ \text{[1]}  - \\ \hline \\ T_{sp} = 25  ^{\circ}\text{C} \\ \hline \\ \text{junction temperature} \\ \hline \\ \text{ambient temperature} \\ \hline \\ \text{storage temperature} \\ \hline \\ \text{Sliode} \\ \hline $	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

12 V, P-channel Trench MOSFET

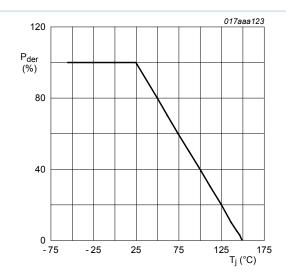


Fig. 2. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$

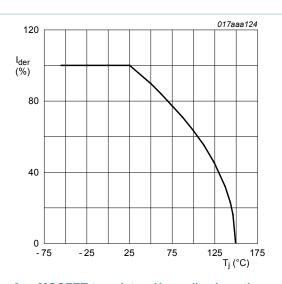


Fig. 3. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

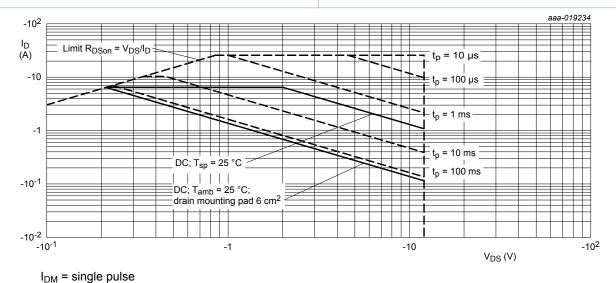


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

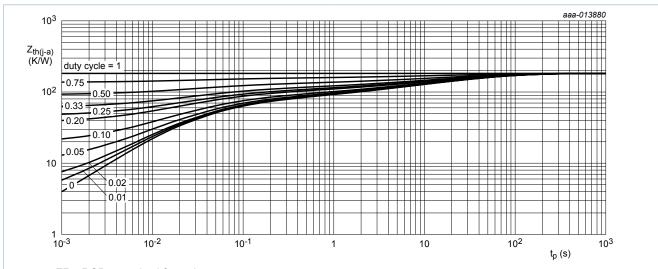
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	180	225	K/W
from junction to ambient	from junction to		[2]	-	65	85	K/W
	ambient		[3]	-	75	95	K/W

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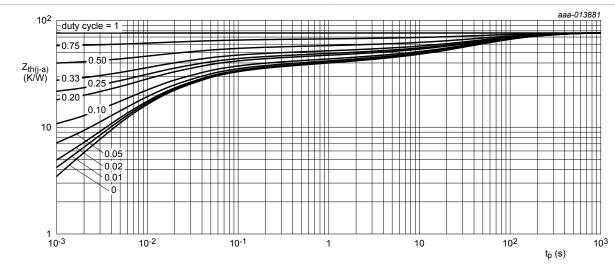
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		in free air; t ≤ 5 s	[3]	-	45	55	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 4-layer 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

**Product data sheet** 

5/15

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.4	-0.6	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -12 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub> gate leakage current	gate leakage current	$V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		$V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-200	nA
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	200	nA
R <sub>DSon</sub> drain-source on-sresistance	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -3.0 A; $T_j$ = 25 °C	-	19	25	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -3.0 A; $T_j$ = 150 °C	-	26	34	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -3.0 A; $T_j$ = 25 °C	-	25	33	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -1.0 A; $T_j$ = 25 °C	-	37	60	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -6.0 V; $I_D$ = -3.0 A; $T_j$ = 25 °C	-	13	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	12.6	-	Ω
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -6 \text{ V}; I_D = -3 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	19.6	29.4	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.7	-	nC
$Q_{GD}$	gate-drain charge		-	5	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -6 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	1400	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	430	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	400	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -6 V; $I_{D}$ = -6 A; $V_{GS}$ = -4.5 V;	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	51	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	72	-	ns
t <sub>f</sub>	fall time		-	62	-	ns
Source-dra	in diode		ı	-	-	
$V_{SD}$	source-drain voltage	$I_S$ = -1.2 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-0.9	-1.2	V

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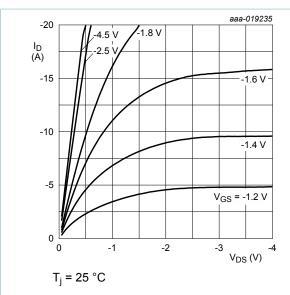
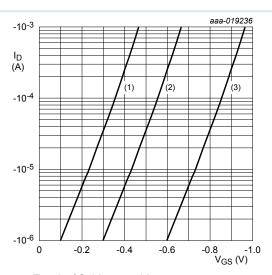


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_j = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage

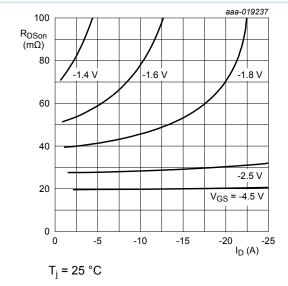


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

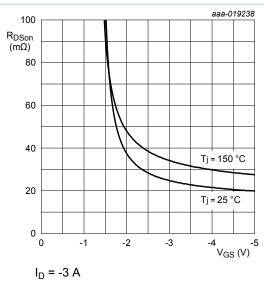


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

12 V, P-channel Trench MOSFET

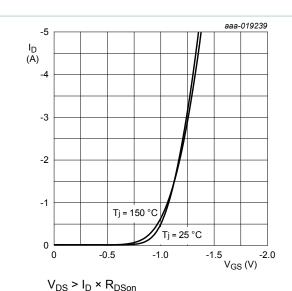


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

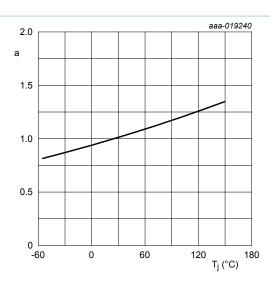
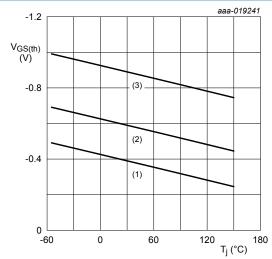


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

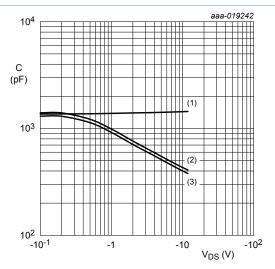
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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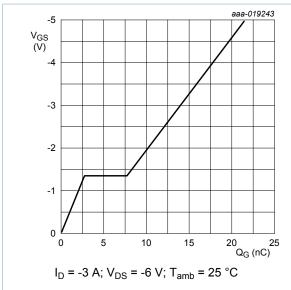


Fig. 15. Gate-source voltage as a function of gate charge; typical values

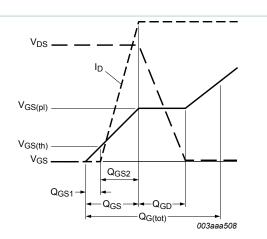


Fig. 16. MOSFET transistor: Gate charge waveform definitions

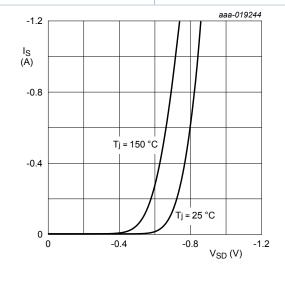
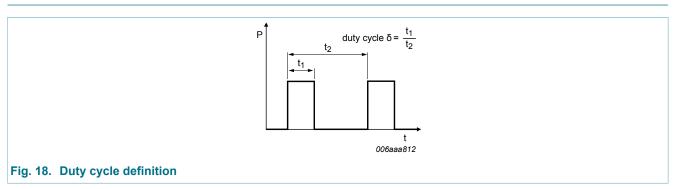


Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 

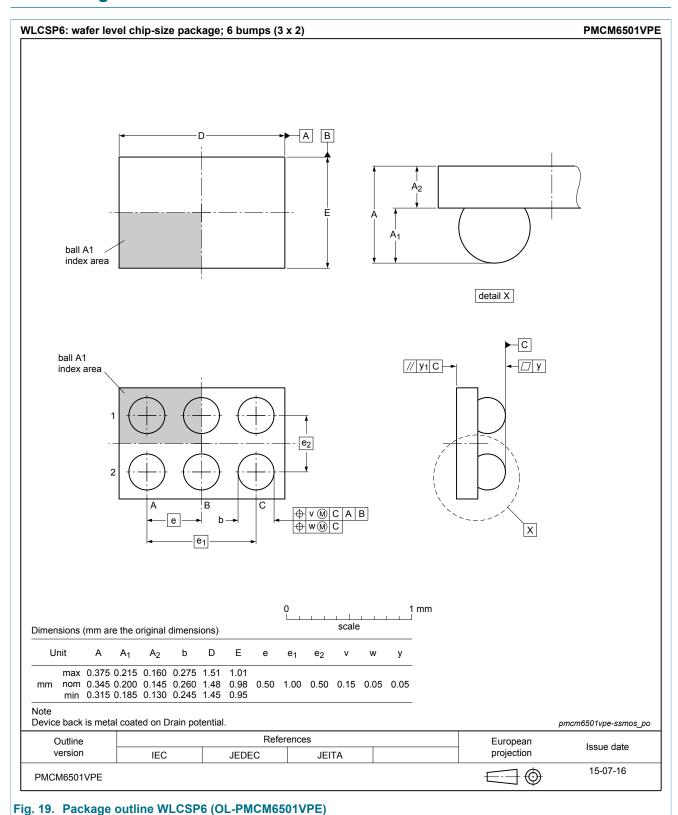


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## 12. Package outline



**Product data sheet** 

10 / 15

## 13. Soldering

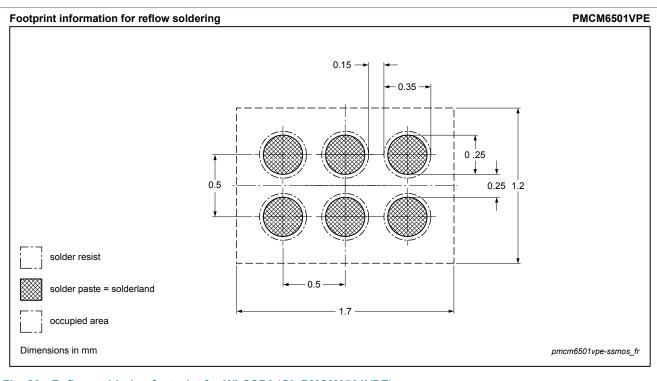


Fig. 20. Reflow soldering footprint for WLCSP6 (OL-PMCM6501VPE)

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMCM6501VPE v.1	20150810	Product data sheet	-	-

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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### 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	
15.3	Disclaimers	13
15.4	Trademarks	14

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